

WHAT IS CLAIMED IS:

1. A method of manufacturing a light emitting device, comprising the steps of:

forming an anode over an insulator;

forming an EL layer over the anode;

subjecting the EL layer to plasma processing; and

forming a cathode over the EL layer subjected to the plasma processing.

2. A method according to claim 1, wherein the plasma processing is carried out by ionizing gas that contains an element for lowering the LUMO level of the EL layer to generate plasma.

3. A method according to claim 1, wherein the plasma processing is carried out by ionizing gas that contains an element for increasing the HOMO level of the EL layer to generate plasma.

4. A method according to claim 1, wherein the plasma processing is carried out by ionizing gas that contains an element belonging to Group 1 or 2 in the periodic table to generate plasma.

5. A method of manufacturing a light emitting device, comprising the steps of:

forming an anode over an insulator;

forming an EL layer over the anode; and

forming a cathode over the EL layer, wherein

the EL layer is formed through a process including forming a first EL film over the anode, subjecting the first EL film to plasma processing, and forming a second EL film over the first EL film subjected to the plasma processing.

6. A method according to claim 5, wherein the plasma processing is carried out by ionizing gas that contains an element for lowering the LUMO level of the EL layer to generate plasma.

7. A method according to claim 5, wherein the plasma processing is carried out by ionizing gas that contains an element for increasing the HOMO level of the EL layer to generate plasma.

8. A method according to claim 5, wherein the plasma processing is carried out by ionizing gas that contains an element belonging to Group 1 or 2 in the periodic table to generate plasma.

9. A method of manufacturing a light emitting device, comprising the steps of:

forming a cathode over an insulator;

forming an EL layer over the cathode;

subjecting the EL layer to plasma processing; and

forming an anode over the EL layer subjected to the plasma processing.

10. A method according to claim 9, wherein the plasma processing is carried out by ionizing gas that contains an element for lowering the LUMO level of the EL layer to generate plasma.

11. A method according to claim 9, wherein the plasma processing is carried out by ionizing gas that contains an element for increasing the HOMO level of the EL layer to generate plasma.

12. A method according to claim 9, wherein the plasma processing is carried out by ionizing gas that contains an element belonging to Group 1 or 2 in the periodic table to generate plasma.

13. A method according to claim 1, wherein the insulator is formed to cover a thin film transistor.

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14. A method according to claim 1, wherein the EL layer includes an organic film that emits light through triplet excitation.

15. A method according to claim 5, wherein the insulator is formed to cover a thin film transistor.

16. A method according to claim 5, wherein the EL layer includes an organic film that emits light through triplet excitation.

17. A method of manufacturing a light emitting device, comprising the steps of:

forming a cathode over an insulator;

forming an EL layer over the cathode; and

forming an anode over the EL layer, wherein

the EL layer is formed through a process including forming a first EL film over the cathode, subjecting the first EL film to plasma processing, and forming a second EL film on the first EL film subjected to the plasma processing.

18. A method according to claim 17, wherein the plasma processing is carried out by ionizing gas that contains an element for lowering the

LUMO level of the EL layer to generate plasma.

19. A method according to claim 17, wherein the plasma processing is carried out by ionizing gas that contains an element for increasing the HOMO level of the EL layer to generate plasma.

20. A method according to claim 17, wherein the plasma processing is carried out by ionizing gas that contains an element belonging to Group 1 or 2 in the periodic table to generate plasma.

21. A method according to claim 17, wherein the insulator is formed to cover a thin film transistor.

22. A method according to claim 17, wherein the EL layer includes an organic film that emits light through triplet excitation.